

LOW FREQUENCY POWER AMPLIFIER

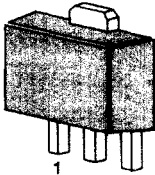
- 3W Output application
- Collector Dissipation $P_C=1\sim 2W$: Mounted on Ceramic Board
- Complement to KSC2883

ABSOLUTE MAXIMUM RATINGS ($T_A=25^{\circ}C$)

Characteristic	Symbol	Rating	Unit
Collector Base Voltage	V_{CBO}	-30	V
Collector-Emitter Voltage	V_{CEO}	-30	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-1.5	mA
Base Current	I_B	-0.3	mA
Collector Dissipation	P_C	500	mW
	P_C^*	1,000	mW
Junction Temperature	T_J	150	$^{\circ}C$
Storage Temperature	T_{STG}	-55 ~ 150	$^{\circ}C$

*Mounted on Ceramic Board(250mm² x 0.8mm)

SOT-89



1. Base 2. Collector 3. Emitter

3

ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}C$)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C = -10mA, I_B = 0$	-30			V
Emitter Base Breakdown Voltage	BV_{EBO}	$I_E = -1mA, I_C = 0$	-5			V
Collector Cut-off Current	I_{CBO}	$V_{CB} = -30V, I_E = 0$			-100	nA
Emitter Cut-off Current	I_{EBO}	$V_{BE} = -5V, I_C = 0$			-100	nA
DC Current Gain	h_{FE}	$V_{CE} = -2V, I_C = -500mA$	100		320	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -1.5A, I_B = -30mA$			-2.0	V
Base Emitter On Voltage	$V_{BE(on)}$	$V_{CE} = -2V, I_C = -500mA$			-1.0	V
Current Gain Bandwidth Product	f_T	$V_{CE} = -2V, I_C = -500mA$		120		MHz
Output Capacitance	C_{OB}	$V_{CB} = -10V, I_E = 0, f = 1MHz$			50	pF

h_{FE} CLASSIFICATION

Classification	O	Y
h_{FE}	100~200	160~320

Marking

